TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7W00F, TC7W00FU

DUAL 2-INPUT NAND GATE

The TC7W00 is a high speed C²MOS 2-INPUT NAND GATE fabricated with silicon gate C²MOS technology.

It achives the high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which enables high noise immunity and stable output.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES

| • | High Speed | $t_{pd} = 6ns (Typ.)$ | at |
|---|------------|---------------------------|----|
| | | Усс = 5V | |

• Low Power Dissipation
$$I_{CC} = 1\mu A$$
 (Max.) at $Ta = 25^{\circ}C$

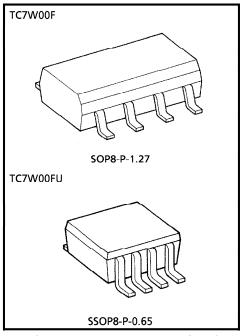
High Noise Immunity
$$V_{NIH} = V_{NIL}$$

= 28% V_{CC} (Min.)

• Symmetrical Output Impedance ...
$$|I_{OH}| = I_{OL} = 4mA$$

• Balanced Propagation Delays $t_{pLH} = t_{pHL}$

Wide Operating Voltage Range ... V_{CC (opr)} = 2~6V

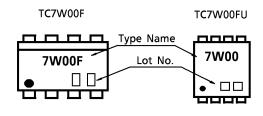


Weight SOP8-P-1.27 : 0.05g (Typ.) SSOP8-P-0.65 : 0.02g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|------------------------------------|------------------|----------------------------|------|
| Supply Voltage Range | Vcc | -0.5~7 | V |
| DC Input Voltage | VIN | -0.5~V _{CC} +0.5 | V |
| DC Output Voltage | Vout | -0.5~V _{CC} + 0.5 | ٧ |
| Input Diode Current | ΙΚ | ± 20 | mA |
| Output Diode Current | loк | ± 20 | mA |
| DC Output Current | IOUT | ± 25 | mΑ |
| DC V _{CC} /Ground Current | lcc | ± 25 | mA |
| Power Dissipation | PD | 300 | mW |
| Storage Temperature | T _{stg} | -65∼150 | °C |
| Lead Temperature (10s) | ΤL | 260 | °C |

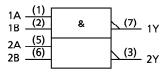
MARKING



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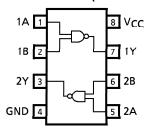
LOGIC DIAGRAM



TRUTH TABLE

| Α | В | Υ |
|---|---|---|
| L | L | Н |
| L | Η | Η |
| Н | L | Н |
| Н | Ι | L |

PIN ASSIGNMENT (TOP VIEW)



RECOMMENDED OPERATING CONDITIONS

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|--------------------------|---------------------------------|--------------------------------|------|
| Supply Voltage | Vcc | 2~6 | V |
| Input Voltage | VIN | 0~V _{CC} | ٧ |
| Output Voltage | Vout | 0~V _{CC} | ٧ |
| Operating Temperature | T _{opr} | - 40~85 | °C |
| | | $0\sim1000 \ (V_{CC}=2.0V)$ | |
| Input Rise and Fall Time | t _r , t _f | $0 \sim 500 \ (V_{CC} = 4.5V)$ | ns |
| | | $0 \sim 400 \ (V_{CC} = 6.0V)$ | |

DC ELECTRICAL CHARACTERISTICS

| CHARACTERISTIC | SYMBOL | TEST CONDITION | | | Т | a = 25° | Ċ | Ta = -4 | 0~85°C | UNIT |
|----------------|-----------------|---|---------------------------|-----|-------------|---------|-------|----------|--------|------|
| CHARACTERISTIC | STIVIBUL | | | ۷сс | MIN. | TYP. | MAX. | MIN. | MAX. | |
| High Loyal | | | | 2.0 | 1.5 | _ | _ | 1.5 | _ | |
| High-Level | ∨ _{IH} | | _ | 4.5 | 3.15 | _ | — | 3.15 | _ | V |
| Input Voltage | | | | 6.0 | 4.2 | _ | _ | 4.2 | _ | |
| Law Laval | | | | 2.0 | _ | _ | 0.5 | _ | 0.5 | |
| Low-Level | VIL | | _ | 4.5 | | _ | 1.35 | | 1.35 | V |
| Input Voltage | | | | 6.0 | | _ | 1.8 | _ | 1.8 | |
| | | | | 2.0 | 1.9 | 2.0 | _ | 1.9 | _ | |
| lug to to the | V _{ОН} | ., ., | $I_{OH} = -20 \mu A$ | 4.5 | 4.4 | 4.5 | — | 4.4 | _ | |
| High-Level | | V _{IN} = V _{IH} or V _{IL} | , | 6.0 | 5.9 | 6.0 | — | 5.9 | _ | V |
| Output Voltage | | | I _{OH} = -4mA | 4.5 | 4.18 | 4.31 | _ | 4.13 | _ | |
| | | | $I_{OH} = -5.2 \text{mA}$ | 6.0 | 5.68 | 5.80 | _ | 5.63 | _ | |
| | | | | 2.0 | _ | 0.0 | 0.1 | | 0.1 | |
| l | | | $I_{OL} = 20 \mu A$ | 4.5 | — | 0.0 | 0.1 | _ | 0.1 | |
| Low-Level | VOL | $V_{IN} = V_{IH}$ | | 6.0 | | 0.0 | 0.1 | <u> </u> | 0.1 | V |
| Output Voltage | | | I _{OL} = 4mA | 4.5 | _ | 0.17 | 0.26 | | 0.33 | |
| | | | $I_{OL} = 5.2 \text{mA}$ | 6.0 | _ | 0.18 | 0.26 | _ | 0.33 | |
| Input Leakage | 1 | V V 4 | or CND | 6.0 | | | ± 0.1 | | ± 1.0 | |
| Current | IN | $V_{IN} = V_{CC}$ or GND | | 0.0 | | | - 0.1 | _ | 1.0 | |
| Quiescent | laa | V V.a.s. 1 | · CND | 6.0 | | | 1.0 | | 10.0 | μΑ |
| Supply Current | lcc | $V_{IM} = V_{CC}$ | עווט וכ | 0.0 | | | 1.0 | | 10.0 | |

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, Ta = 25°C)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | Т | UNIT | | |
|-------------------|------------------|----------------|------|------|------|------|
| CHARACTERISTIC | STIVIBUL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
| Output Transition | tTLH | | | 4 | ۰ | nc |
| Time | tTHL | _ | | 4 | ° | ns |
| Propagation Delay | t _{pLH} | | | 6 | 12 | |
| Time | t _{pHL} | _ | _ | 0 | 12 | ns |

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

| CHARACTERISTIC | SYMBOL | DL TEST CONDITION | | Ta = 25°C | | | Ta = -4 | UNIT | |
|-------------------------------|------------------|-------------------|-----|--------------|------|------|--------------|------|------|
| CHARACTERISTIC | 3 I WIBOL | | | MIN. | TYP. | MAX. | MIN. | MAX. | ONIT |
| Output Transition | t | | 2.0 | _ | 25 | 75 | _ | 95 | |
| 1 | t _{TLH} | _ | 4.5 | — | 7 | 15 | _ | 19 | ns |
| Time | ^t THL | | 6.0 | — | 6 | 13 | _ | 16 | |
| Dramagation Dalay | 4 | | 2.0 | _ | 27 | 75 | _ | 95 | |
| Propagation Delay Time | t _{pLH} | <u> </u> | 4.5 | | 9 | 15 | - | 19 | ns |
| rime | t _{pHL} | | 6.0 | — | 8 | 13 | _ | 16 | |
| Input Capacitance | CIN | _ | | _ | 5 | 10 | _ | 10 | |
| Power Dissipation Capacitance | C _{PD} | (Note 1) | | _ | 20 | _ | _ | _ | pF |

Note 1 : CpD is defined as the value of internal equivalent capacitance of IC which is calculated from the operating current consumption without load (refer to Test Circuit).

Average operating current can be obtained by the equation hereunder. $I_{CC \text{ (opr)}} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 2 \text{ (per gate)}$